



PNP Darlington Power Silicon Transistor

Qualified per MIL-PRF-19500/505

Qualified Levels:
JAN, JANTX, and
JANTXV

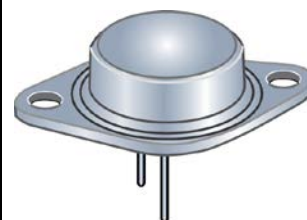
DESCRIPTION

This high speed PNP transistor is rated at 20 amps and is military qualified up to a JANTXV level. This TO-204AA isolated package features a 180 degree lead orientation.

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FEATURES

- JEDEC registered 2N6286 and 2N6287
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/505
- RoHS compliant versions available (commercial grade only)



**TO-204AA (TO-3)
Package**

APPLICATIONS / BENEFITS

- Military, space and other high reliability applications
- High frequency response
- TO-204AA case with isolated terminals

MAXIMUM RATINGS @ $T_C = +25^\circ\text{C}$ unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-65 to +175	$^\circ\text{C}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.855	$^\circ\text{C/W}$
Collector Current	I_C	-20	A
Collector-Emitter Voltage	V_{CEO}	2N6286 -80	V
		2N6287 -100	
Collector-Base Voltage	V_{CBO}	2N6286 -80	V
		2N6287 -100	
Emitter-Base Voltage	V_{EBO}	-7	V
Total Power Dissipation	P_T	@ $T_C = +25^\circ\text{C}$ ⁽¹⁾ 175	W
		@ $T_C = +100^\circ\text{C}$ 87.5	

Notes: 1. Derate linearly 1.0 W/ $^\circ\text{C}$ above $T_C > +25^\circ\text{C}$

MSC – Lawrence
6 Lake Street,
Lawrence, MA 01841
1-800-446-1158
(978) 620-2600
Fax: (978) 689-0803

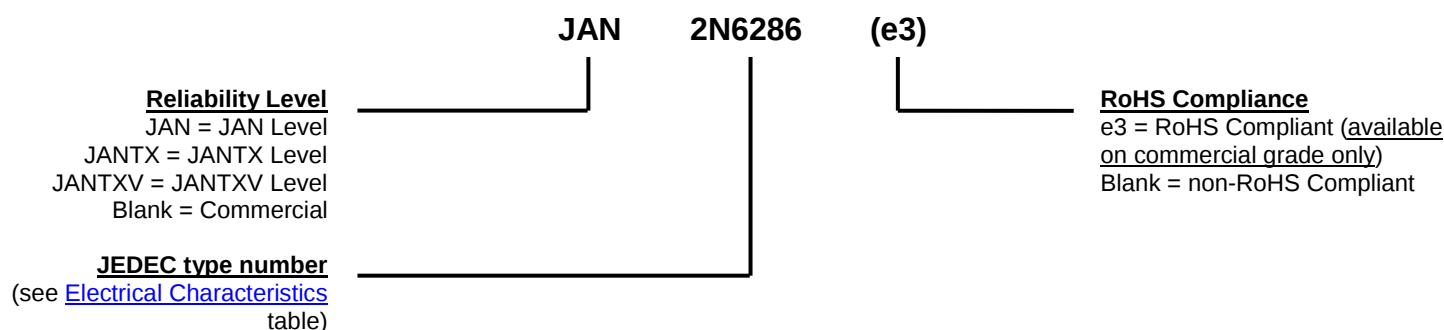
MSC – Ireland
Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:
www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Industry standard TO-204AA (TO-3), hermetically sealed, 0.040 inch diameter pins
- FINISH: Solder dipped tin-lead over nickel plated alloy 52 or RoHS compliant matte-tin plating. Solderable per MIL-STD-750 method 2026.
- POLARITY: PNP (see [schematic](#))
- MOUNTING HARDWARE: Consult factory for optional insulator and sheet metal screws
- WEIGHT: Approximately 15 grams
- See [package dimensions](#) on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
I_B	Base current: The value of the dc current into the base terminal.
I_C	Collector current: The value of the dc current into the collector terminal.
I_E	Emitter current: The value of the dc current into the emitter terminal.
T_C	Case temperature: The temperature measured at a specified location on the case of a device.
V_{CB}	Collector-base voltage: The dc voltage between the collector and the base.
V_{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
V_{CC}	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.
V_{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
V_{EB}	Emitter-base voltage: The dc voltage between the emitter and the base.
V_{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$ unless otherwise noted

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = -100\text{ mA}$	2N6286 2N6287	$V_{(BR)CEO}$	-80 -100	V
Collector-Emitter Cutoff Current $V_{CE} = -40\text{ V}$ $V_{CE} = -50\text{ V}$	2N6286 2N6287	I_{CEO}	-1.0 -1.0	mA
Collector-Emitter Cutoff Current $V_{CE} = -80\text{ V}, V_{BE} = +1.5\text{ V}$ $V_{CE} = -100\text{ V}, V_{BE} = +1.5\text{ V}$	2N6286 2N6287	I_{CEX}	10 10	μA
Emitter-Base Cutoff Current $V_{EB} = -7.0\text{ V}$		I_{EBO}	-2.5	mA

ON CHARACTERISTICS

Forward-Current Transfer Ratio $I_C = -1.0\text{ A}, V_{CE} = -3.0\text{ V}$ $I_C = -10\text{ A}, V_{CE} = -3.0\text{ V}$ $I_C = -20\text{ A}, V_{CE} = -3.0\text{ V}$		h_{FE}	1,500 1,250 300	18,000	
Collector-Emitter Saturation Voltage $I_C = -20\text{ A}, I_B = -200\text{ mA}$ $I_C = -10\text{ A}, I_B = -40\text{ mA}$		$V_{CE(sat)}$	-3.0 -2.0		V
Base-Emitter Saturation Voltage $I_C = -20\text{ A}, I_B = -200\text{ mA}$		$V_{BE(sat)}$	-4.0		V
Base-Emitter Voltage Non-saturated $V_{CE} = -3.0\text{ V}, I_C = -10\text{ A}$		V_{BE}	-2.8		V

DYNAMIC CHARACTERISTICS

Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -10\text{ A}, V_{CE} = -3.0\text{ V}, f = 1\text{ kHz}$		h_{fe}	300		
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -10\text{ A}, V_{CE} = -3.0\text{ V}, f = 1\text{ MHz}$		$ h_{fe} $	8	80	
Output Capacitance $V_{CB} = -10\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1\text{ MHz}$		C_{obo}		400	pF

ELECTRICAL CHARACTERISTICS @ $T_C = 25^\circ\text{C}$ unless otherwise noted. (continued)**SWITCHING CHARACTERISTICS**

Turn-On Time $V_{CC} = -30\text{ V}$, $I_C = -10\text{ A}$; $I_B = -40\text{ mA}$	t_{on}		2.0	μs
Turn-Off Time $V_{CC} = -30\text{ V}$, $I_C = -10\text{ A}$; $I_{B1} = I_{B2} = -40\text{ mA}$	t_{off}		10	μs

SAFE OPERATING AREA (See figures 1 and 2 and [MIL-STD-750, Test Method 3053](#))**DC Tests** $T_C = +25^\circ\text{C}$, $t = 1\text{ second}$, 1 Cycle**Test 1** $V_{CE} = -8.75\text{ V}$, $I_C = -20\text{ A}$ **Test 2** $V_{CE} = -30\text{ V}$, $I_C = -5.8\text{ A}$ **Test 3** $V_{CE} = -80\text{ V}$, $I_C = -100\text{ mA}$ (2N6286) $V_{CE} = -100\text{ V}$, $I_C = -100\text{ mA}$ (2N6287)

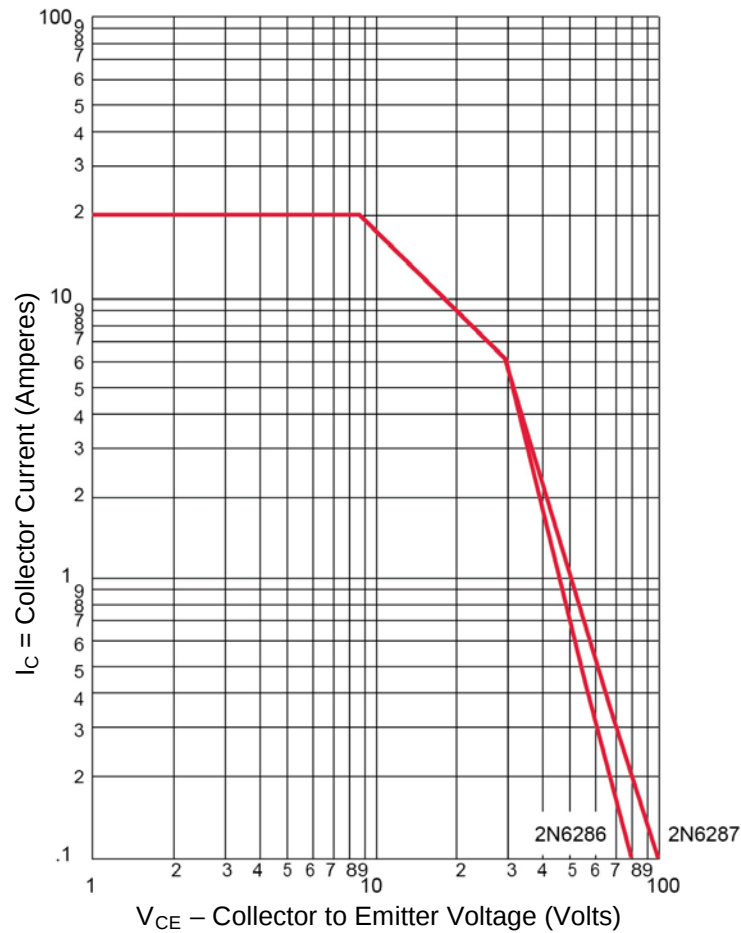
SAFE OPERATING AREA


FIGURE 1
Maximum Safe Operating Area Graph
 (continuous dc)

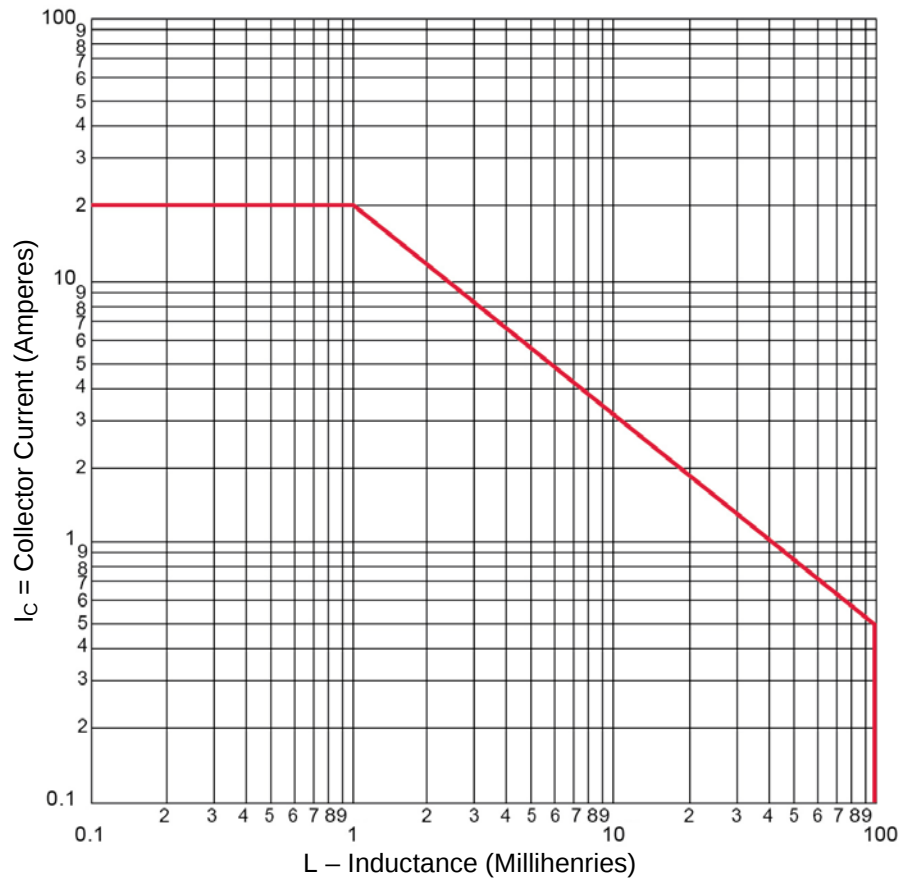
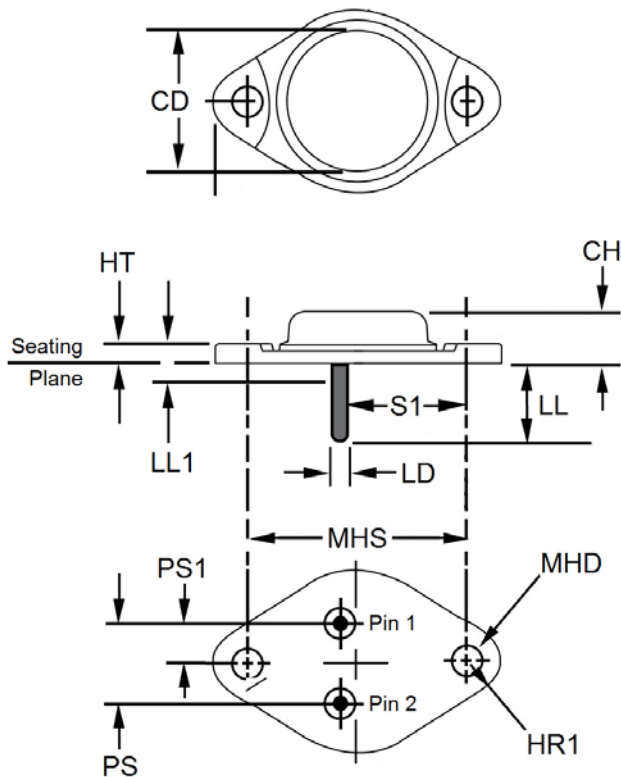
SAFE OPERATING AREA (continued)


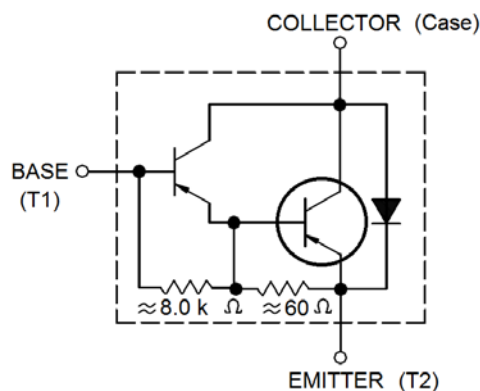
FIGURE 2
Safe Operating Area For Switching Between Saturation And Cutoff
(unclamped inductive load).

PACKAGE DIMENSIONS


Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	-	0.875	-	22.23	3
CH	0.250	0.360	6.35	9.14	
HR	0.495	0.525	12.57	13.34	
HR1	0.131	0.188	3.33	4.78	
HT	0.060	0.135	1.52	3.43	
LD	0.038	0.043	0.97	1.09	4, 8
LL	0.312	0.500	7.92	12.70	4
LL1	-	0.050	-	1.27	4, 8
MHD	0.151	0.165	3.84	4.19	6
MHS	1.177	1.197	29.90	30.40	
PS	0.420	0.440	10.67	11.18	3
PS1	0.205	0.225	5.21	5.72	
S1	0.655	0.675	16.64	17.15	
T1	Emitter				
T2	Base				
Case	Collector				

NOTES:

1. Dimensions are in inches. Millimeters are given for information only.
2. Body contour is optional within zone defined by CD
3. These dimensions shall be measured at points 0.050 inch (1.27 mm) to 0.055 inch (1.40 mm) below seating plane.
4. Both terminals
5. At both ends
6. Two holes
7. Terminal 1 is the emitter, terminal 2 is base. The collector shall be electrically connected to the case.
8. LD applies between L1 and LL. Diameter is uncontrolled in L1.
9. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

SCHEMATIC


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